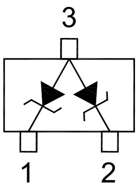
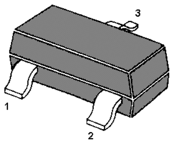
SAD500CA

Silicon Epitaxial Planar Diodes

Electrostatic Discharge Surge Absorber Diodes





1. Cathode 2. Cathode 3. Anode
Marking Code: **500**
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	200	mW
Surge Reverse Power (t = 10 µs, 1 Pulse)	P_{RSM}	2	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Electrical Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I_R = 1 mA	$V_{(BR)R}$	5.3	8	-	V
Reverse Current at V_R = 3 V	I_R	-	-	0.1	µA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	-	3.5	-	pF
ESD Immunity Level [1)] at C = 150 pF, R = 330 Ω (Contact Discharge)	-	8	-	-	KV

[1)] Biased Upon with IEC 61000-4-2.

Figure1. 1vs .VBO CHARACTERISTICS

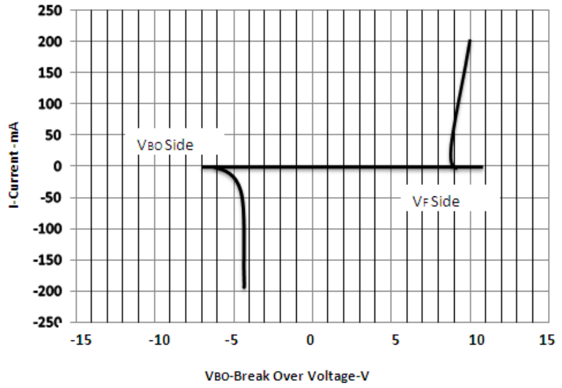


Figure 2. Ct vs. V CHARACTERISTICS

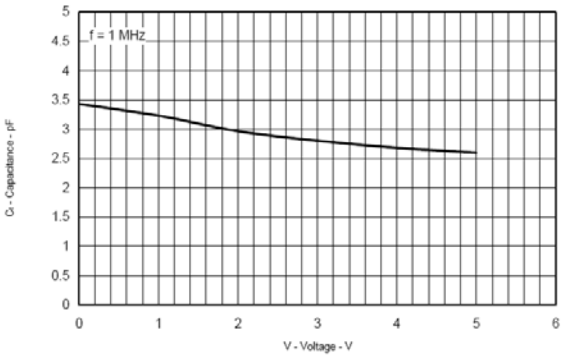


Figure3. It vs .V CHARACTERISTICS